

## AMENDMENT

### Claim Amendments

1. (canceled)
2. (canceled)
3. (currently amended) A dual gate NMOS device, comprising
  - a drain,
  - a source,
  - a first gate between the drain and the source,
  - a second gate between the drain and the source, wherein the first gate is closer to the drain and the second gate is closer to the source, and
  - a lightly doped n-type region having a lower doping level than the drain, extending towards the drain from the gate edge that lies closest to the drain for the first gate, ~~wherein the length of the lightly doped region is between 0.18  $\mu\text{m}$  and 0.5  $\mu\text{m}$  and~~ wherein the drain includes a drain silicide and a n+ drain ballasting region extending between the drain silicide and the lightly doped region.
4. (previously presented) A device of claim 3 , wherein the length of the lightly doped region is between 0.18  $\mu\text{m}$  and 0.25  $\mu\text{m}$ .
5. (previously presented) A device of claim 3, wherein the lightly doped region extends from the drain to the first gate.
6. (canceled)
7. (currently amended) A method of reducing soft leakage current degradation in a NMOS snapback device that has at least one gate, a n+ drain and a n+ source, comprising
  - providing for a n-lightly doped region between the gate and the n+ drain of the device, that has a length substantially the same as the n+ drain depth, wherein

the n-lightly doped region is formed from an NLDD region by masking a region between the gate and the drain during n+ doping of the drain.

8. (previously presented) A method of claim 7, wherein the n-lightly doped region is formed to extend substantially from the edge of the gate for  $0.18\ \mu\text{m} - 0.5\ \mu\text{m}$ .
9. (previously presented) A method of claim 8, wherein the n-lightly doped region is formed to extend substantially from the edge of the gate for  $0.18\ \mu\text{m} - 0.25\ \mu\text{m}$ .
10. (previously presented) A method of claim 7, wherein the mask comprises ~~may comprise~~ a standard mask used in the process such as n+ composite and silicide exclusion mask.
11. (previously presented) A method of claim 3, wherein the NMOS device is ~~may be~~ a multiple gate device in which the lightly doped region is located between the drain and the gate nearest the drain.